

Surface Mount RF PIN Diodes

Technical Data

HSMP-383x Series

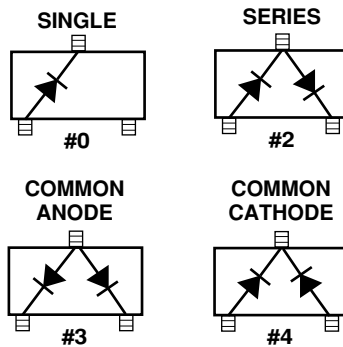
Features

- **Diodes Optimized for:**
Low Capacitance Switching
Low Current Attenuator
- **Surface Mount SOT-23 Package**
Single and Dual Versions
Tape and Reel Options
Available
- **Low Failure in Time (FIT) Rate¹**
- **Lead-free Option Available**

Note:

1. For more information see the Surface Mount PIN Reliability Data Sheet.

Package Lead Code Identification (Top View)



Description/Applications

The HSMP-383x series of general purpose PIN diodes are designed for two classes of applications. The first is attenuators where current consumption is the most important design consideration. The second application for this series of diodes is in switches where low capacitance is the driving issue for the designer.

The HSMP-386x series Total Capacitance (C_T) and Total Resistance (R_T) are typical specifications. For applications that require guaranteed performance, the general purpose HSMP-383x series is recommended.

A SPICE model is not available for PIN diodes as SPICE does not provide for a key PIN diode characteristic, carrier lifetime.

Absolute Maximum Ratings^[1] $T_C = 25^\circ\text{C}$

Symbol	Parameter	Units	Absolute Maximum
I_F	Forward Current (1 ms Pulse)	Amp	1
P_t	Total Device Dissipation	mW ^[2]	250
P_{IV}	Peak Inverse Voltage	—	Same as V_{BR}
T_j	Junction Temperature	$^\circ\text{C}$	150
T_{STG}	Storage Temperature	$^\circ\text{C}$	-65 to 150

Notes:

1. Operation in excess of any one of these conditions may result in permanent damage to this device.
2. CW Power Dissipation at $T_{LEAD} = 25^\circ\text{C}$. Derate to zero at maximum rated temperature.

PIN General Purpose Diodes, Electrical Specifications $T_C = 25^\circ\text{C}$

Part Number HSMP-	Package Marking Code ^[1]	Lead Code	Configuration	Minimum Breakdown Voltage V_{BR} (V)	Maximum Series Resistance R_S (Ω)	Maximum Total Capacitance C_T (pF)
3830	K0	0	Single	200	1.5	0.3
3832	K2	2	Series			
3833	K3	3	Common Anode			
3834	K4	4	Common Cathode			
Test Conditions				$V_R = V_{BR}$ Measure $I_R \leq 10$ mA	$I_F = 100$ mA $f = 100$ MHz	$V_R = 50$ V $f = 1$ MHz

Typical Parameters at $T_C = 25^\circ\text{C}$

Part Number HSMP-	Series Resistance R_S (Ω)	Carrier Lifetime τ (ns)	Reverse Recovery Time T_{rr} (ns)	Total Capacitance C_T (pF)
383x	20	500	80	0.20 @ 50 V
Test Conditions	$I_F = 1$ mA $f = 100$ MHz	$I_F = 50$ mA $I_R = 250$ mA	$V_R = 10$ V $I_F = 20$ mA 90% Recovery	

Note:

1. Package marking code is white.

Typical Parameters at $T_C = 25^\circ\text{C}$ (unless otherwise noted), Single Diode

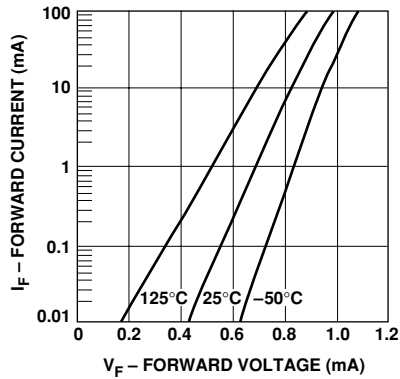


Figure 1. Forward Current vs. Forward Voltage.

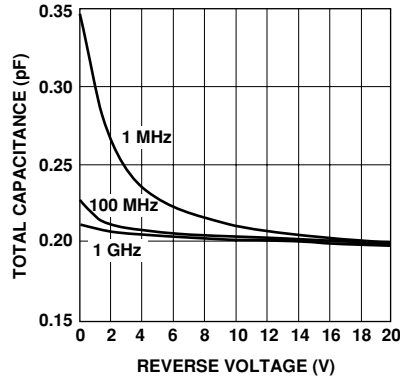


Figure 2. RF Capacitance vs. Reverse Bias.

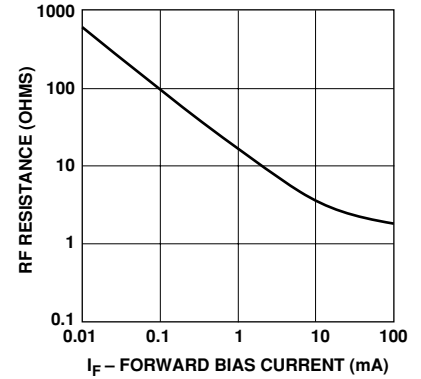


Figure 3. RF Resistance at 25°C vs. Forward Bias Current.

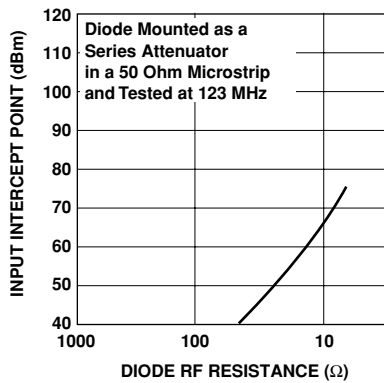


Figure 4. 2nd Harmonic Input Intercept Point vs. Diode RF Resistance for Attenuators.

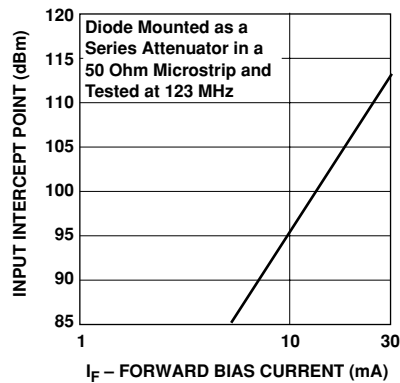


Figure 5. 2nd Harmonic Input Intercept Point vs. Forward Bias Current for Switches.

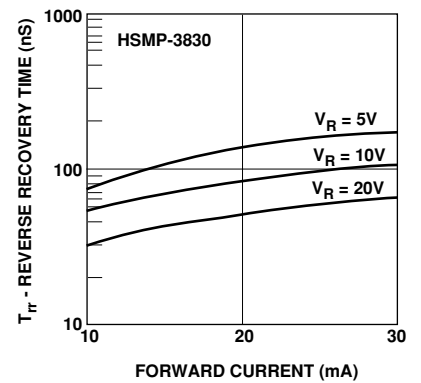


Figure 6. Reverse Recovery Time vs. Forward Current for Various Reverse Voltage.

Typical Applications for Multiple Diode Products

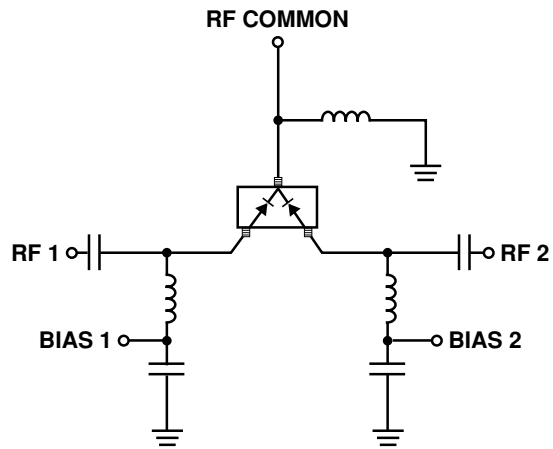


Figure 7. Simple SPDT Switch, Using Only Positive Current.

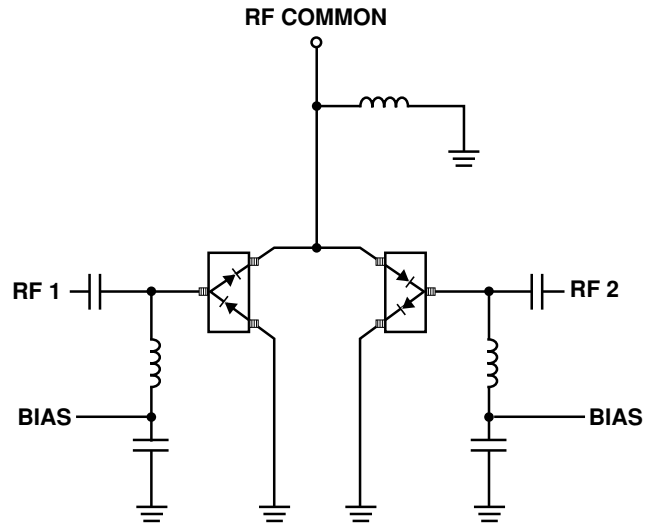


Figure 8. High Isolation SPDT Switch, Dual Bias.

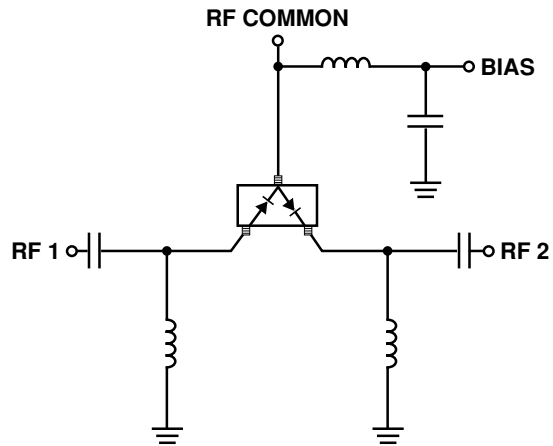


Figure 9. Switch Using Both Positive and Negative Current.

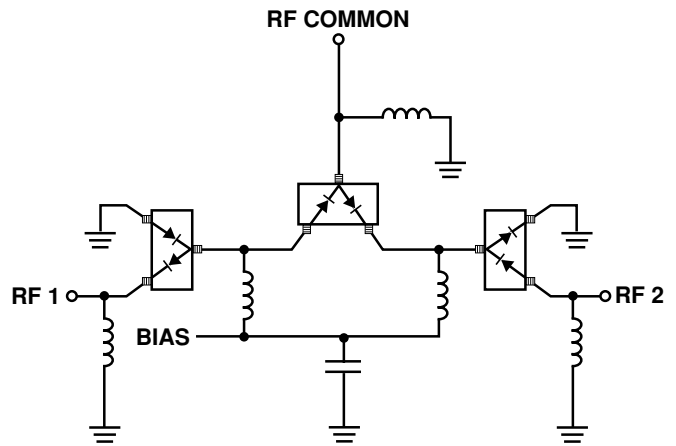


Figure 10. Very High Isolation SPDT Switch, Dual Bias.

Typical Applications for Multiple Diode Products (continued)

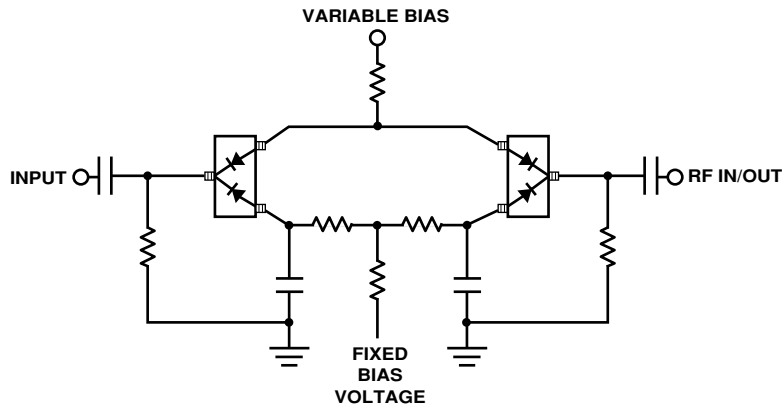


Figure 11. Four Diode π Attenuator. See AN1048 for details.

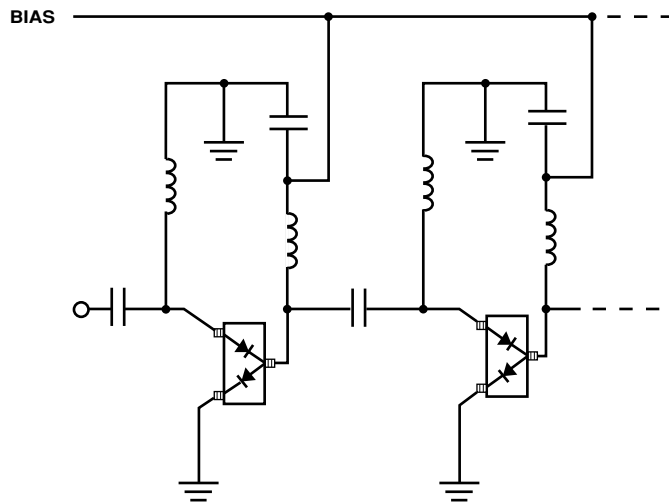


Figure 12. High Isolation SPST Switch
(Repeat Cells as Required).

Device Orientation For Outlines SOT-23

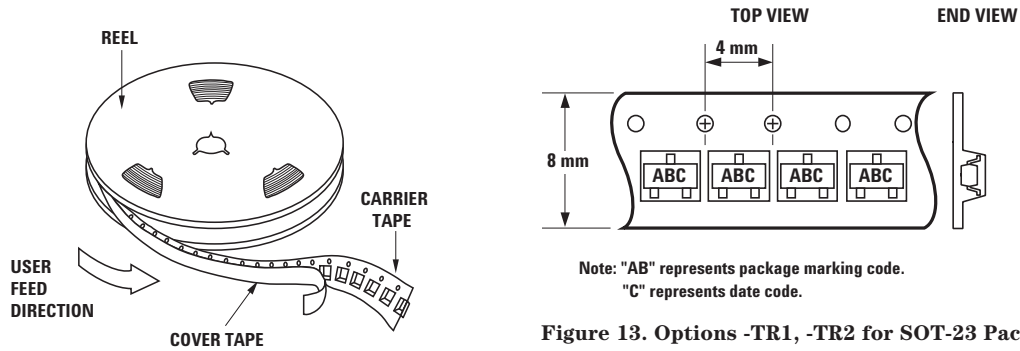
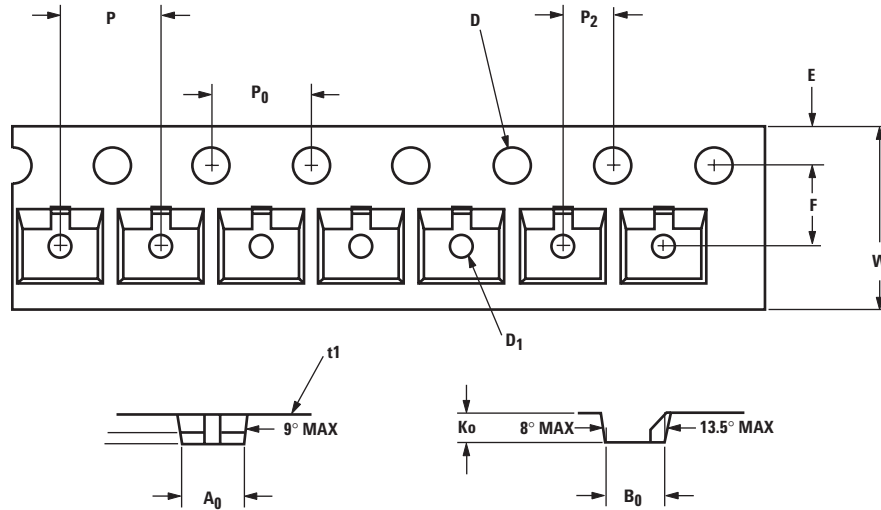


Figure 13. Options -TR1, -TR2 for SOT-23 Packages.

Tape Dimensions and Product Orientation For Outline SOT-23



	DESCRIPTION	SYMBOL	SIZE (mm)	SIZE (INCHES)
CAVITY	LENGTH	A ₀	3.15 ± 0.10	0.124 ± 0.004
	WIDTH	B ₀	2.77 ± 0.10	0.109 ± 0.004
	DEPTH	K ₀	1.22 ± 0.10	0.048 ± 0.004
	PITCH	P	4.00 ± 0.10	0.157 ± 0.004
	BOTTOM HOLE DIAMETER	D ₁	1.00 + 0.05	0.039 ± 0.002
PERFORATION	DIAMETER	D	1.50 + 0.10	0.059 + 0.004
	PITCH	P ₀	4.00 ± 0.10	0.157 ± 0.004
	POSITION	E	1.75 ± 0.10	0.069 ± 0.004
CARRIER TAPE	WIDTH	W	8.00 + 0.30 - 0.10	0.315 + 0.012 - 0.004
	THICKNESS	t ₁	0.229 ± 0.013	0.009 ± 0.0005
DISTANCE BETWEEN CENTERLINE	CAVITY TO PERFORATION (WIDTH DIRECTION)	F	3.50 ± 0.05	0.138 ± 0.002
	CAVITY TO PERFORATION (LENGTH DIRECTION)	P ₂	2.00 ± 0.05	0.079 ± 0.002

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Data subject to change.

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